

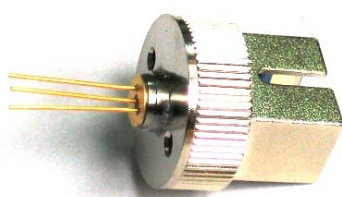
InGaAs PIN Module

Features

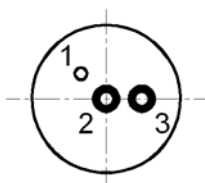
Active diameter 300um
Small dark current
High reliability

Applications

Fiberoptics telecommunication networks
Digital receivers
Optical interconnects
Test and measurement
Datacom



PIN assignment



pin	Function
1(case)	GND
2	N
3	P

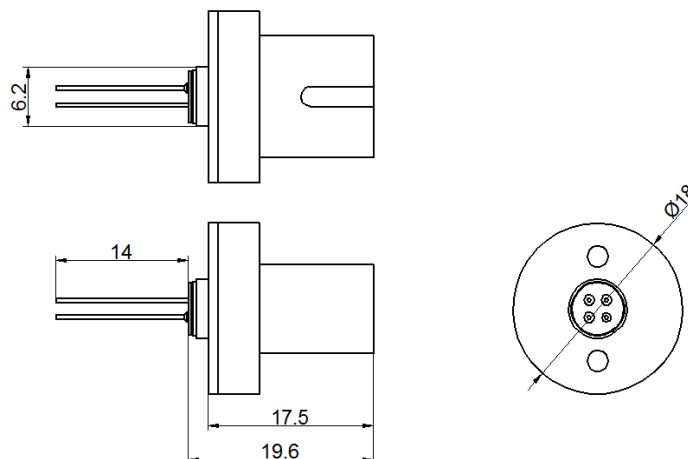
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Storage temperature	T _{st}	-40~+85	°C
Operating temperature	T _{op}	-40~+85	°C
Reverse voltage	V _R	30	V
Soldering temperature/time	—	260/10	°C/ s

Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Detection range	λ	1100	-	1650	nm	-
Dark current	I _d	-	0.1	1	nA	V _R =5V
Quantum efficiency	R	0.80	0.85	-	A/W	V _R =5V, λ =1310 nm
Capacitance	C _t	-	-	0.75	pF	V _R =5V

Dimensions Diagram



This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures



Order information

D	1	03	X	B
			Range 0,-70~+6dBm 1, -60~+10dBm 2, -50~+20dBm	Package S,S

Copyright © 2008 by shinebon